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Vishay Semiconductor/Diodes Division SD200N12PV

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Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of SD200N12PV - DIODE GEN PURP 1.2KV 200A DO205

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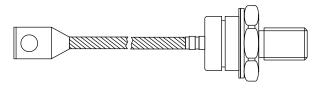


www.vishay.com

VS-SD200N/R Series

Vishay Semiconductors

Standard Recovery Diodes (Stud Version), 200 A



DO-205AC (DO-30)

| PRODUCT SUMMARY | | | | | |
|-----------------------|------------------|--|--|--|--|
| I _{F(AV)} | 200 A | | | | |
| Package | DO-205AC (DO-30) | | | | |
| Circuit configuration | Single diode | | | | |

FEATURES

- Wide current range
- High voltage ratings up to 2400 V
- High surge current capabilities
- · Stud cathode and stud anode version
- Standard JEDEC[®] types
- Compression bonded encapsulations
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- Converters
- Power supplies
- · Machine tool controls
- High power drives
- · Medium traction applications

| MAJOR RATINGS AND CHARACTERISTICS | | | | | |
|-----------------------------------|-----------------|-------------------|-------|--------|--|
| | TEST CONDITIONS | VS-SD20 | UNITS | | |
| PARAMETER | | 1600 to 2000 | 2400 | | |
| 1 | | 200 | | A | |
| I _{F(AV)} | T _C | 110 | | °C | |
| I _{F(RMS)} | | 314 | | | |
| 1 | 50 Hz | 4700 | | А | |
| IFSM | 60 Hz | 4920 | | | |
| 121 | 50 Hz | 110 | | 1.42- | |
| l ² t | 60 Hz | 101 | | – kA²s | |
| V _{RRM} | Range | 1600 to 2000 2400 | | V | |
| TJ | | -40 to 180 | 150 | °C | |

ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS | | | | | | | | |
|-----------------|-----------------|--|--|--|--|--|--|--|
| TYPE NUMBER | VOLTAGE CODE | V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V | V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V | I _{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA | | | | |
| | 16 | 1600 | 1700 | | | | | |
| VS-SD200N/R | 20 | 2000 | 2100 | 15 | | | | |
| | 24 | 2400 | 2500 | | | | | |

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| FORWARD CONDUCTION | | | | | | | |
|--|---------------------|---|--|---|--------|---------------------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | | | VALUES | UNITS | |
| Naximum average forward current | | | | 200 | Α | | |
| at case temperature | | 190º oondu | uction half sing | 110 | °C | | |
| Maximum average forward current | I _{F(AV)} | | duction, half sine wave | 220 | А | | |
| at case temperature | | | | | 100 | °C | |
| Maximum RMS forward current | I _{F(RMS)} | DC at 95 ° | C case tempera | ature | 314 | | |
| | | t = 10 ms | No voltage | - | 4700 | | |
| Maximum peak, one-cycle forward, | | t = 8.3 ms | reapplied | | 4920 | А | |
| non-repetitive surge current | I _{FSM} | t = 10 ms | 100 % V _{RRM} reapplied | | 3950 | | |
| | | t = 8.3 ms | | Sinusoidal half wave, initial T _J = T _J maximum | 4140 | | |
| | l ² t | t = 10 ms | No voltage | | 110 | | |
| Maximum I ² t for fusing | | t = 8.3 ms | reapplied | | 101 | — kA ² s | |
| Maximum int for fusing | | t = 10 ms | 100 % V _{BBM} | | 78 | | |
| | | t = 8.3 ms | reapplied | | 71 | | |
| Maximum I ² \sqrt{t} for fusing | l²√t | t = 0.1 to 1 | 0 ms, no voltag | e reapplied | 1100 | kA²√s | |
| Low level value of threshold voltage | V _{F(TO)1} | (16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum | | 0.90 | v | | |
| High level value of threshold voltage | V _{F(TO)2} | $(I > \pi \times I_{F(AV)}), T_J = T_J maximum$ | | | 1.00 | | |
| Low level value of forward slope resistance | r _{f1} | (16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum | | 0.79 | mΩ | | |
| High level value of forward slope resistance | r _{f2} | $(I > \pi x I_{F(AV)}), T_J = T_J maximum$ | | | 0.64 | | |
| Maximum forward voltage drop | V _{FM} | | λ, T _J = T _J maxin sinusoidal wav | | 1.40 | V | |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | | |
|--|-------------------|---|------------|------------|--------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | SD200 | UNITS | | |
| FARAMEIER | | 1600 to 2000 | 2400 | UNITS | | |
| Maximum junction operating temperature range | TJ | | -40 to 180 | -40 to 150 | °C | |
| Maximum storage temperature range | T _{Stg} | - 55 to 200 | | 200 | | |
| Maximum thermal resistance, junction to case | R _{thJC} | DC operation | 0.23 | | K/W | |
| Maximum thermal resistance, case to heatsink | R _{thCS} | Mounting surface, smooth, flat and greased 0.08 | | 3 | r./ vv | |
| Maximum allowed mounting torque ± 10 % | | Not-lubricated threads 14 | | | Nm | |
| Approximate weight | | | 120 | | g | |
| Case style | | See dimensions (link at the end of datasheet) | DO-20 | 5AC (DO-30 |)) | |

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| CONDUCTION ANGLE | SINUSOIDAL CONDUCTION | RECTANGULAR CONDUCTION | TEST CONDITIONS | UNITS | | | |
|------------------|-----------------------|------------------------|---------------------|-------|--|--|--|
| 180° | 0.041 | 0.030 | | | | | |
| 120° | 0.049 | 0.051 | | | | | |
| 90° | 0.063 | 0.068 | $T_J = T_J maximum$ | K/W | | | |
| 60° | 0.093 | 0.096 | | | | | |
| 30° | 0.156 | 0.157 | | | | | |

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

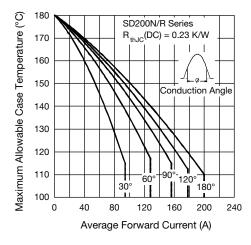


Fig. 1 - Current Ratings Characteristics

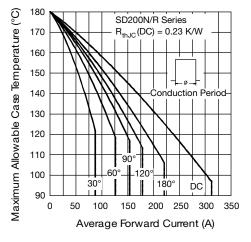


Fig. 2 - Current Ratings Characteristics

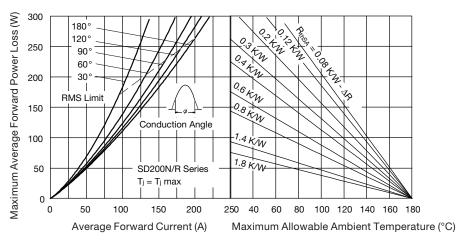


Fig. 3 - Forward Power Loss Characteristics

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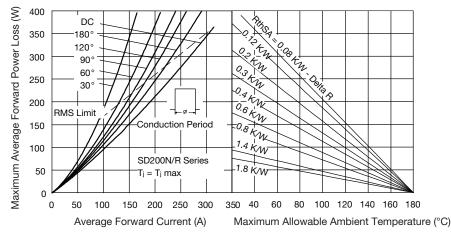
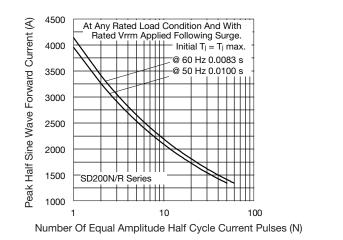
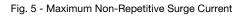


Fig. 4 - Forward Power Loss Characteristics





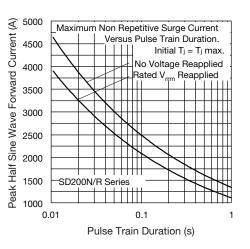
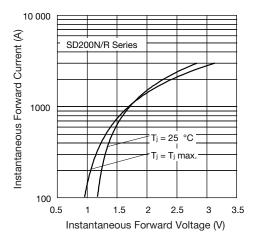
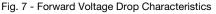


Fig. 6 - Maximum Non-Repetitive Surge Current





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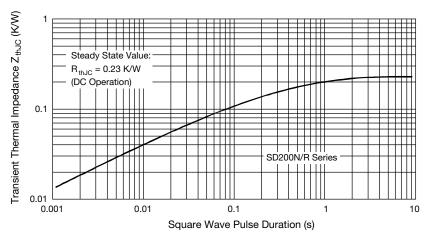


Fig. 8 - Thermal Impedance ZthJC Characteristic

ORDERING INFORMATION TABLE

| Device code | vs- | SD | 20 | 0 | N | 24 | Ρ | с |
|-------------|---------------------------------|--|---------------------|----------------------------------|---------------------|----------|---------|---------------------|
| | | 2 | 3 | 4 | 5 | 6 | 7 | 8 |
| | 1 - 2 - 3 - 4 - 5 - | Vishay Semiconductors product Diode Essential part number 0 = Standard recovery • N = Stud normal polarity (cathode to stud) | | | | | | |
| | 6 - 7 - | Voltag | e code : | verse po x 100 = ` se DO-2 | V _{RRM} (s | ee Volta | age Rat | ings tabl JNF-2A |
| | 8 - | | Stud ba eramic h | se DO-2 iousing | 205AC (I | DO-30) | M12 x ′ | 1.75 |

For metric device M12 x 1.75 contact factory

| LINKS TO RELATED DOCUMENTS | | | | |
|----------------------------|--------------------------|--|--|--|
| Dimensions | www.vishay.com/doc?95302 | | | |

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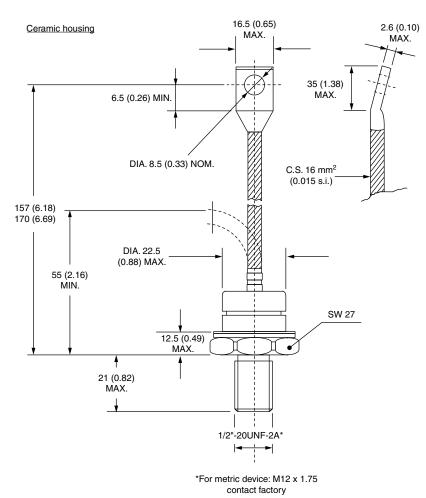


Outline Dimensions

Vishay Semiconductors

DO-205AC (DO-30)

DIMENSIONS in millimeters (inches)







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